



SE12S3BDD3GH

ESD Protection Diode

FEATURES

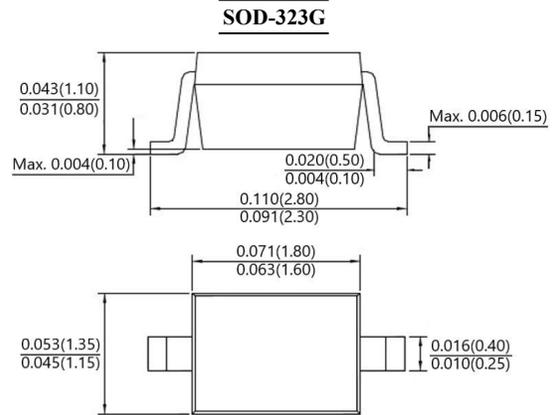
- 350W Peak Pulse Power per Line ($t_p=8/20\mu s$)
- IEC61000-4-2(ESD) $\pm 15kV$ (air), $\pm 8kV$ (Contact)
- Protect One Power or I/O Port
- Bi-directional Configurations
- Suffix " H " indicated Halogen-free part, ex.SE12S3BDD3GH

APPLICATIONS

- Audio and video equipment
- Communication system
- Cellular handsets and accessories

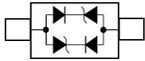
MECHANICAL DATA

Case : SOD-323G



Dimensions in inchs and (millimeters)

PIN CONFIGURATION



Maximum Ratings (Rating at 25°C ambient temperature unless otherwise specified)

Parameter	Symbol	Value	Units
Peak Pulse Power ($t_p=8/20\mu s$)	P_{PP}	350	W
ESD per IEC 61000-4-2 (Air)	V_{ESD}	± 15	kV
ESD per IEC 61000-4-2 (Contact)		± 8	
Peak Pulse Current ($t_p=8/20\mu s$)	I_{PP}	12	A
Operating Junction Temperature	T_J	-55 to +125	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C



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Electrical Characteristics (Rating at 25°C ambient temperature unless otherwise specified)

Parameter	Test Condition	Symbol	Min	Typ.	Max	Units
Reverse Stand-Off Voltage	-	V_{RWM}	-	-	12.0	V
Reverse Breakdown Voltage	$I_R = 1\text{mA}$	$V_{(BR)}$	13.5	-	-	V
Reverse Leakage Current	$V_{RWM} = 3\text{V}$	I_R	-	-	1	μA
Clamping Voltage	$I_{PP} = 1\text{A}, t_p = 8/20\mu\text{s}$	V_C	-	-	19.0	V
	$I_{PP} = 12\text{A}, t_p = 8/20\mu\text{s}$		-	-	28.6	
Capacitance	$f = 1\text{MHz}$	C_J	-	-	3	pF

RATINGS AND CHARACTERISTIC CURVES

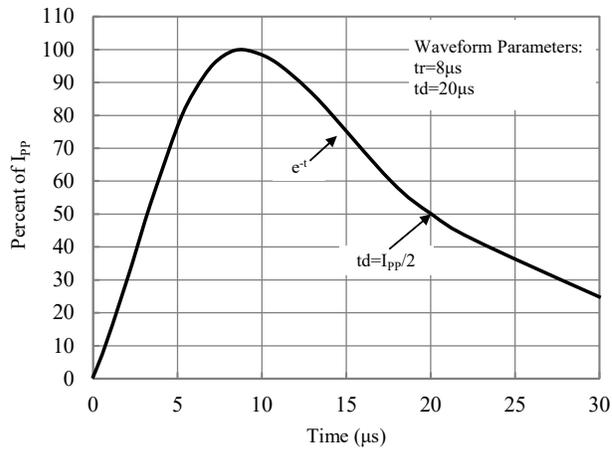


Fig.1-Pulse Waveform

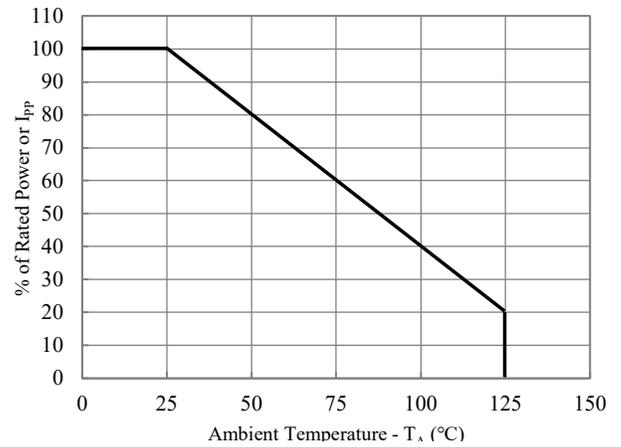


Fig.2-Power Derating Curve